



Is Now Part of



**ON Semiconductor®**

To learn more about ON Semiconductor, please visit our website at  
[www.onsemi.com](http://www.onsemi.com)

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at [www.onsemi.com](http://www.onsemi.com). Please email any questions regarding the system integration to [Fairchild\\_questions@onsemi.com](mailto:Fairchild_questions@onsemi.com).

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.



# FFG3105

## Battery ID and Smart Charge Monitor

### Features

- Two, One-Time-Programmable, 64-Bit Registers for Unique Identifier Codes.
- Precision Voltage and Temperature Measurement enables Smart Charging Topologies
- Low Power: < 2  $\mu$ A Shutdown Current  
2  $\mu$ A Standby Current  
< 4.5  $\mu$ A Average Active Current
- Fully Integrated I<sup>2</sup>C Slave with support for Normal and Fast Modes with auto increment.
- Internal BID redundancy for increased robustness
- 6-Ball, 2 x 3, 0.5 mm Pitch - Chip Scale Packaging (WLCSP)

### Applications

- Battery Packs
- Mobile Devices

### Description

The FFG3105 battery ID and smart charge monitor chip is designed for battery packs used in cell phones and other mobile devices. The FFG3105 has two programmable 64-bit registers, which can be used to store a pack's identification code. The FFG3105 monitors the cell voltage and temperature providing precise knowledge of these values. This information can be used in charging applications to ensure optimal performance and safety.

The FFG3105 includes an integrated temperature sensor and battery voltage monitor. The FFG3105 also includes twelve 16-bit registers which can be used to store battery parameters and recent history. A system side fuel gauge like Fairchild's FFG1040 can use these registers to facilitate fast initialization following battery removal and reinsertion or for battery swaps. All registers including temperature and voltage readings can be accessed by the host via I<sup>2</sup>C in either Standard-mode or Fast-mode.

Each Battery ID register has an internal redundant copy to improve robustness and protect against potential miss programming.

The FFG3105 utilizes a 2 x 3 ball, 0.5 mm pitch, WLCSP with nominal dimensions of 0.96 x 1.66 mm<sup>2</sup>.

### Ordering Information

Part Number	Operating Temperature Range	Package	Packing Method
FFG3105UCX	-40 to 85°C	0.96 x 1.66 mm <sup>2</sup> , 6-Ball CSP, 0.5 mm Ball Pitch	Tape and Reel

## Block Diagram

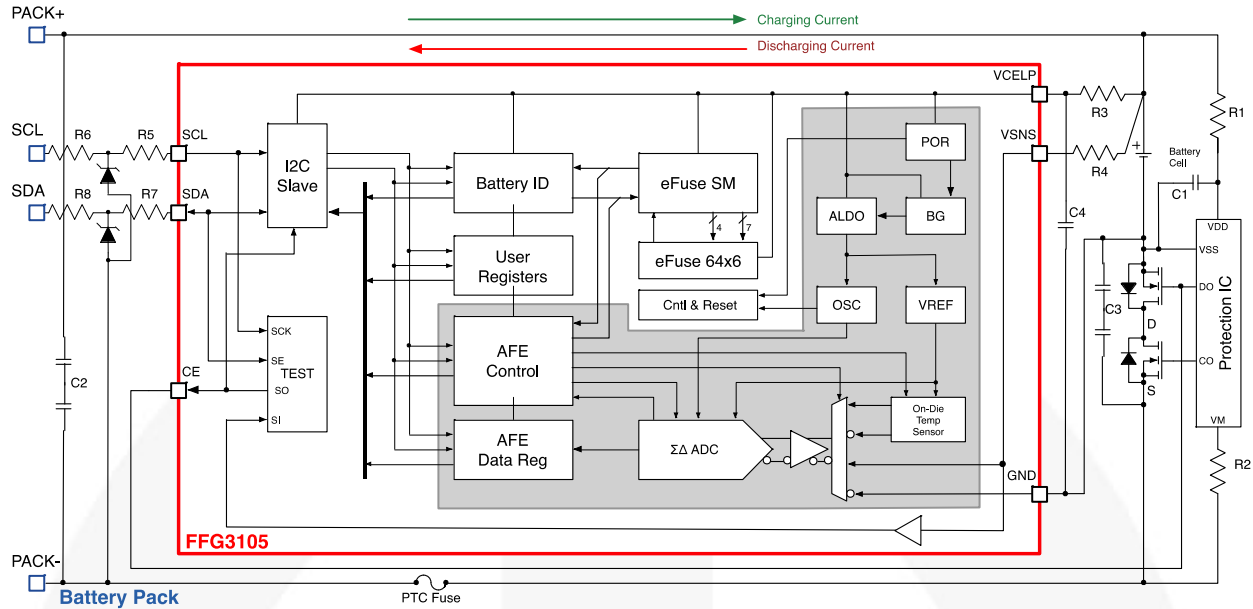


Figure 1. FFG3105 Block Diagram and Battery Pack

Table 1. Recommended External Components

Component	Description	Typical	Unit
R1	Protection IC ESD Protection and power fluctuation Resistor <sup>(1)</sup>	220	Ω
R2	Protection IC Protection for reverse connection of charger <sup>(1)</sup>	1000	Ω
R3	VCELP ESD Series Protection Resistor	300	Ω
R4	VSNS ESD Series Protection Resistor	1000	Ω
R5, R6, R7, R8	SCL and SDA ESD Protection Resistor	100	Ω
C1	Decoupling Capacitor for power fluctuation <sup>(1)</sup>	0.1	μF
C2 <sup>(2)</sup>	ESD Protection Capacitor	0.1	μF
C3	ESD Protection Capacitor <sup>(1)</sup>	0.1	μF
C4	Decoupling Capacitor for power fluctuation	0.1	μF

### Notes:

1. Please follow the recommendation of the Protection IC vendor for these component values.
2. C2 should consist of two capacitors in series as shown in Figure 1 in the event one of the capacitors were to short circuit.

## Pin Configuration

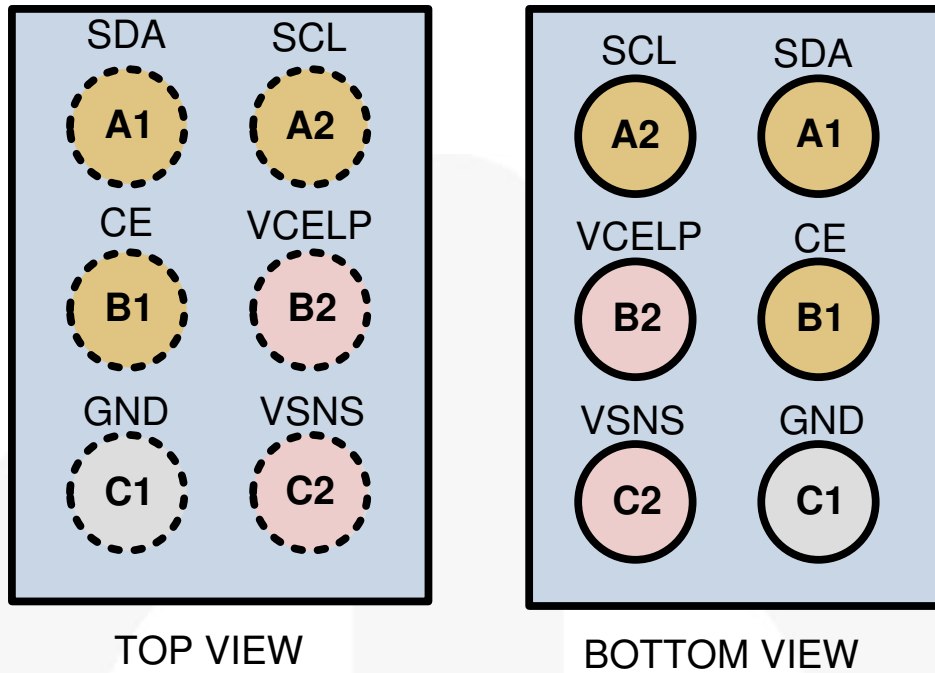


Figure 2. Ball Assignments

## Pin Definitions

Name	Position	Type	Description
CE	B1	Digital I/O	<b>Chip Enable.</b> Connected to Battery Protection IC and used to enable and disable the device. This pin should not be left floating.
GND	C1	Ground	<b>Device Ground.</b> Connected to Battery Cell Anode
SCL	A2	Digital I/O	<b>I<sup>2</sup>C Serial Clock,</b> I <sup>2</sup> C communication clock input. This pin should not be left floating, use with 2-10 k pull up resistor.
SDA	A1	Digital I/O	<b>I<sup>2</sup>C Serial Data,</b> Bi-directional I <sup>2</sup> C serial data line. This pin should not be left floating, use with 2-10 k pull up resistor.
VCELP	B2	Power	<b>Power Input.</b> Decoupled with 0.1 μF to GND and connected to Battery Cell Cathode through a series protection resistor.
VSNS	C2	Sense Input	<b>Voltage Sense.</b> Battery Voltage Measurement Sense ADC Input. Connected to Battery Cell Cathode through series protection resistor.

## Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Min.	Max.	Unit
V <sub>CELP</sub>	Positive Battery Supply Voltages	V <sub>GND</sub> - 0.5	V <sub>GND</sub> + 6.0	V
V <sub>GND</sub>	Negative Analog Supply Voltage	V <sub>CELP</sub> - 6.0	V <sub>CELP</sub> + 0.5	V
V <sub>I/O</sub>	All Digital Input / Output Signals	V <sub>GND</sub> - 0.5	V <sub>GND</sub> + 6.0	V
T <sub>A</sub>	Operating Free-air Temperature	-40	+85	°C
T <sub>JMAX</sub>	Maximum Junction Temperature		+150	°C
T <sub>STG</sub>	Storage Temperature Range	-65	+150	°C
T <sub>L</sub>	Lead Soldering Temperature, 10 Seconds		+260	°C
ESD	Human Body Model, ANSI/ESDA/JEDEC JS-001-2012	2		kV
	Charged Device Model, JESD22-C101	500		V
	IEC 6100-4-2 System ESD, Pins VIN <sup>(3)</sup>	Air Gap	15	kV
		Contact	8	kV

### Note:

3. Pins should be protected by external TVS devices when tested for IEC compliance.

## Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings. The recommended operating conditions assume the following: V<sub>CELP</sub> = 2.5 V to 4.5 V, T<sub>A</sub> = -40°C to +85°C, unless otherwise noted.

Symbol	Parameter	Min.	Max.	Unit
V <sub>CELP</sub>	Battery Supply Voltage	2.5	4.5	V
	Device Programming Voltage	5.5	6.0	V
V <sub>BAT_SLEW</sub>	Battery Supply Voltage Slew Rate	20		V/ms
R <sub>I2CPU</sub>	I <sup>2</sup> C Pull up Resistor to V <sub>PU</sub> (SDA, SCL)	4.7	10	kΩ
C <sub>b</sub>	I <sup>2</sup> C Bus Capacitance for each pin		400	pF
T <sub>A</sub>	Operating Free-air Temperature	-40	+85	°C
T <sub>J</sub>	Operating Junction Temperature	-40	+85	°C

## Thermal Properties

Junction-to-ambient thermal resistance is a function of application and board layout. This data is measured with four-layer 2s2p boards in accordance to JEDEC standard JESD51. Special attention must be paid not to exceed junction temperature T<sub>J(max)</sub> at a given ambient temperature T<sub>A</sub>.

Symbol	Parameter	Typical	Unit
θ <sub>JA</sub>	Junction-to-Ambient Thermal Resistance (1in. <sup>2</sup> pad of 2 oz. copper)	70	°C/W
θ <sub>JB</sub>	Junction-to-PCB Thermal Resistance	20	°C/W

## DC Electrical Characteristics

The Recommended Operating Conditions for DC Electrical Characteristics assume  $V_{CELP} = 2.5\text{ V to }4.5\text{ V}$  and  $T_A = -20^\circ\text{C to }70^\circ\text{C}$ , unless otherwise noted. Typical values are at  $T_A = 25^\circ\text{C}$ ,  $V_{CELP} = 3.8\text{ V}$ .  $V_{PU} = V_{CELP}$ . Min. / Max. values are guaranteed by design and/or characterization for process variations and the temperature range of  $T_A = -20^\circ\text{C to }70^\circ\text{C}$ .

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_{IN}$	Input Leakage Current on Digital I/O Pins	$0 \leq V_{IN} \leq V_{CELP}$ ; $V_{CELP} = 2.5\text{ to }4.5\text{ V}$			0.5	$\mu\text{A}$
$I_{OFF}$	Power-Off Leakage Current (Shutdown)	$V_{IN}$ or $V_{OUT} = 4.5\text{ V}$ ; $V_{CELP} = 0$		0.2	< 2.0	$\mu\text{A}$
$I_{CC}$	Standby Mode Current <sup>(4,10)</sup>	$V_{IN} = 3.6\text{ V}$ ; $V_{CELP} = 2.5\text{ to }4.5\text{ V}$		2.0	4.0	$\mu\text{A}$
	Active Mode Average Current <sup>(4,5,10)</sup>			4.3	7.0	
<b>Fast Mode(400 KHz) I<sup>2</sup>C Controller SDA, SCL, (<math>T_A = -40^\circ\text{C to }85^\circ\text{C}</math>)</b>						
$V_{IL}$	Low-Level Input Voltage <sup>(8, 9)</sup>		-0.50		0.65	V
$V_{IH}$	High-Level Input Voltage <sup>(8, 9)</sup>		1.05		4.50	V
$V_{OL}$	Low-Level Output Voltage at 3 mA Sink Current (Open Drain) <sup>(6,9)</sup>	$V_{CELP} > 2\text{ V}$	0		0.4	V
		$V_{CELP} < 2\text{ V}$			$0.2 \times V_{CELP}$	
$V_{PU}$	External Pull Up Voltage Range		1.62		4.50	V
$I_I$	Input Current of Each I/O Pin, Input Voltage 0.26 V to 2.34 V		-10		10	$\mu\text{A}$
$C_I$	Capacitance for Each I/O Pin <sup>(10)</sup>				10	pF
<b>CE (<math>T_A = -40^\circ\text{C to }85^\circ\text{C}</math>)</b>						
$V_{IL}$	Low-Level Input Voltage		-0.5		$0.3 \times V_{CELP}$	V
$V_{IH}$	High-Level Input Voltage		$0.7 \times V_{CELP}$		$V_{CELP} + 0.5$	V
$I_I$	Input Current, Input Voltage 0.26 V to 2.34 V		-10		10	$\mu\text{A}$
$C_I$	Capacitance <sup>(10)</sup>				10	pF

Continued on the following page...

### DC Electrical Characteristics (Continued)

The Recommended Operating Conditions for DC Electrical Characteristics assume  $V_{CELP} = 2.5\text{ V to }4.5\text{ V}$  and  $T_A = -20^\circ\text{C to }70^\circ\text{C}$ , unless otherwise noted. Typical values are at  $T_A = 25^\circ\text{C}$ ,  $V_{CELP} = 3.8\text{ V}$ .  $V_{PU} = V_{CELP}$ . Min. / Max. values are guaranteed by design and/or characterization for process variations and the temperature range of  $T_A = -20^\circ\text{C to }70^\circ\text{C}$ .

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>Data Acquisition Performance Parameters</b>						
$T_{MIN}, T_{MAX}$	Temperature Range		-40		85	$^\circ\text{C}$
$G_{TEMP}$	Temperature Sensor Voltage Gain <sup>(10)</sup>			2.0		mV/ $^\circ\text{C}$
$T_{DIE}$	Temperature Measurement Error <sup>(10,11)</sup>	$V_{CELP} = 2.5\text{ to }4.5\text{ V}$ , $T_A = +25^\circ\text{C}$	-2		+2	$^\circ\text{C}$
		$T_A = +0^\circ\text{C}$	-3		+3	$^\circ\text{C}$
		$T_A = +50^\circ\text{C}$	-3		+3	$^\circ\text{C}$
		$T_A = -40^\circ\text{C}$	-4		+4	$^\circ\text{C}$
		$T_A = +80^\circ\text{C}$	-4		+4	$^\circ\text{C}$
LSB	Voltage Sense Least Significant Bit				122	$\mu\text{V}$
EVR	Voltage Measurement Resolution	$V_{CELP} = 2.5\text{ to }4.5$			1	mV
$V_{GERR}$	Voltage Gain Error (% of  VBAT- 3.5 V )	$V_{CELP} = 2.5\text{ to }4.5$	-0.85		+0.85	%
$V_{OS}$	Voltage Offset Error	$V_{CELP} = 2.5\text{ to }4.5\text{ V}$ $T_J = -20\text{ }^\circ\text{C to }+70^\circ\text{C}$	-20		+20	mV

**Notes:**

4. Assumes I<sup>2</sup>C access at 400 kHz rate.
5. Average active current is based on request for voltage and temperature measurement once per every 2 seconds.
6. The SDA and SCL pins are open drain with external pull-up resistor tied to VPU. Recommended pull-up resistor range is 4.7 k $\Omega$  to 10 k $\Omega$ .
7.  $V_{IH(max.)} = V_{PU} + 0.5$  or 5.5 V which-ever is lower.
8.  $V_{IH}$  and  $V_{IL}$  have been chosen to be fully compliant to I2C specification at  $V_{PU} = 1.8\text{ V} \pm 10\%$ . At  $2.25\text{ V} \leq V_{PU} \leq 3.63\text{ V}$  the  $V_{IL(max.)}$  provides 200 mV of noise margin to the required  $V_{OL(max.)}$  of the transmitter.
9. Parts may be ordered for enhanced I2C operation in systems where the device I2C pull-up resistors are biased from a voltage greater than 3.6 V. Please contact Fairchild for parts programmed with this feature.
10. Guaranteed by design; not tested in production.
11. Accuracy (expressed in  $^\circ\text{C}$ ) = the difference between the FFG3105 output temperature and the measured temperature.

## AC Electrical Characteristics (I<sup>2</sup>C Controller SDA, SCL)

The AC electrical characteristics assume  $V_{CELP} = 2.5\text{ V}$  to  $4.5\text{ V}$ .

Symbol	Parameter	Fast Mode		
		Min.	Max.	Unit
$f_{SCL}$	SCL Clock Frequency	0	400	kHz
$t_{HD,STA}$	Hold Time (Repeated) Start Condition	0.6		$\mu\text{s}$
$t_{LOW}$	Low Period of SCL Clock	1.3 <sup>(12)</sup>		$\mu\text{s}$
$t_{HIGH}$	High Period of SCL Clock	0.6		$\mu\text{s}$
$t_{SU,STA}$	Set-up Time for Repeated Start Condition	0.6		$\mu\text{s}$
$t_{HD,DAT}$	Data Hold Time (see Figure 3)	0	0.9	$\mu\text{s}$
$t_{SU,DAT}$	Data Set-up Time (see Figure 3)	100 <sup>(13)</sup>		ns
$t_{PS}$	Set-up Time Required by SDA Input Buffer (Receiving Data)	0		ns
$t_{PH}$	Out Delay Required by SDA Output Buffer (Transmitting Data)	300		ns
$t_r$	Rise Time of SDA and SCL Signals	$20+0.1C_b^{(14,15)}$	300	ns
$t_f$	Fall Time of SDA and SCL Signals	$20+0.1C_b^{(14,15)}$	300	ns
$t_{SU,STO}$	Set-up Time for Stop Condition	0.6		$\mu\text{s}$
$t_{BUF}$	Bus Free Time between a Stop and Start Conditions	1.3		$\mu\text{s}$
$t_{SP}$	Pulse Width of Spikes that Must Be Suppressed by the Input Filter	0	50	ns

### Notes:

12. The FFG3105 can accept clock signals with  $t_{LOW}$  as low as  $1.1\ \mu\text{s}$ , provided that the received SDA signal  $t_{HD,DAT} + t_{r,f} \leq 1.1\ \mu\text{s}$ . The FFG3105 features a  $0\text{ ns}$  SDA input set-up time; therefore, this parameter is not included in the above equation.
13. A Fast-Mode I<sup>2</sup>C Bus® device can be used in a Standard-Mode I<sup>2</sup>C bus system, but the requirement that  $t_{SU,DAT} \geq 250\text{ ns}$  must be met. This is automatically the case if the device does not stretch the LOW period of the SCL signal. If a device does stretch the LOW period of the SCL signal, it must output the next data bit to the SDA line  $t_{r,max} + t_{SU,DAT} = 1000 + 250 = 1250\text{ ns}$  (according to the Standard-Mode I<sup>2</sup>C Bus specification) before the SCL line is released.
14.  $C_b$  equals the total capacitance of one bus line in pF.
15. The FFG3105 ensures that the SDA signal OUT must coincide with SCL LOW for worst-case SCL  $t_{f,max}$  time of  $300\text{ ns}$ . This requirement prevents data loss by preventing SDA-OUT transitions during the undefined region of the falling edge of SCL. Consequently, the FFG3105 fulfills the following requirement from the I<sup>2</sup>C specification (page 77, Note 2): "A device must internally provide a hold time of at least  $300\text{ ns}$  for the SDA signal (referred to the  $V_{IHmin}$  of the SCL signal) to bridge the undefined region of the falling edge of SCL."
16. FFG3105 I<sup>2</sup>C slave is fully compliant the NXP (Phillips) I<sup>2</sup>C specification, Rev. 0.3 UM10204 (2007) for both Standard Mode and Fast Mode.
17. The FFG3105 is tested and qualified for a max speed of  $400\text{ Kbps/s}$ , Fast Mode.

### Timing Diagrams

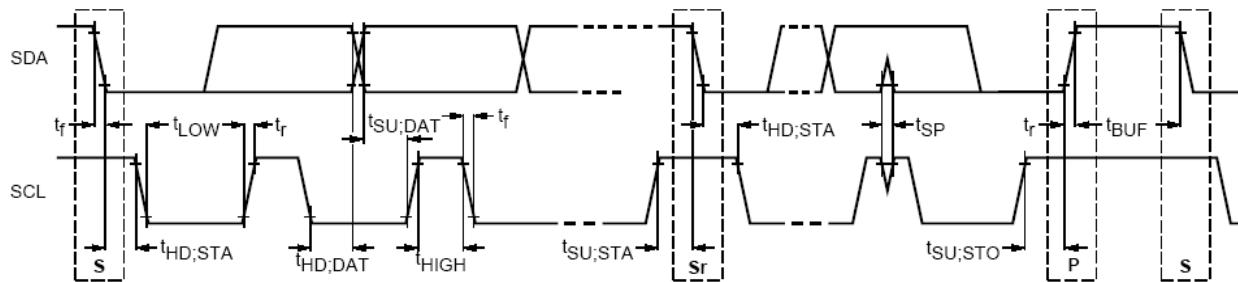


Figure 3. Definition of Timing for Full-Speed Mode Devices on the I<sup>2</sup>C Bus



## System Applications Diagram

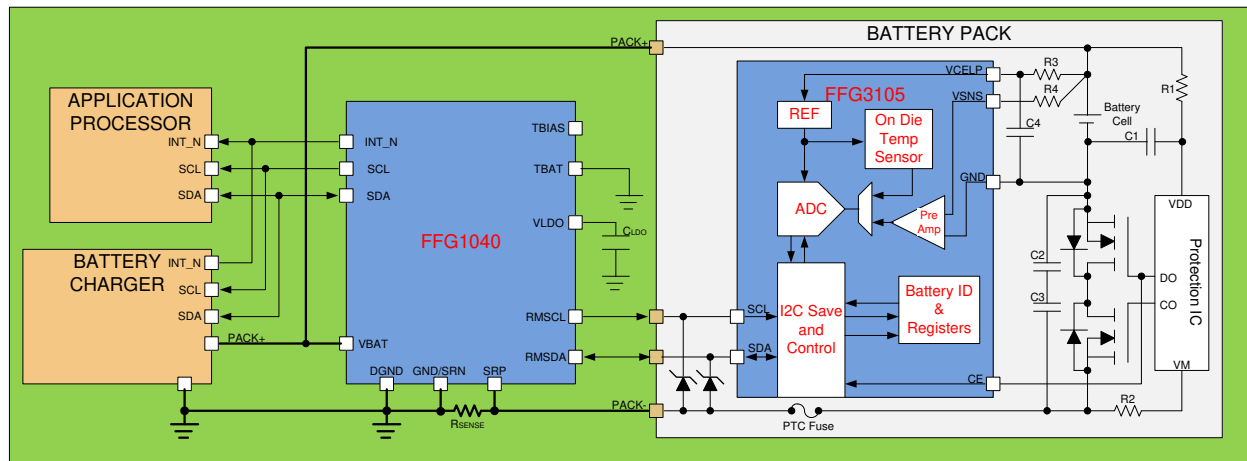


Figure 4. Systems Applications Diagram

## Functional Description

### Overview

The FFG3105 includes a 64-bit one-time factory programmable fuse locked register to enable unique battery identification.

The FFG3105 uses an Analog-to-Digital Converter (ADC) to monitor the battery cell voltage and temperature.

### Battery Pack Identification

The FFG3105 has two 64-bit, one-time programmable registers for Battery ID (BID). These registers can be programmed with customized values by battery lot or phone model. With the ability to uniquely identify specific batteries, systems can selectively enable special features after verifying that the system battery is valid.

Each register has an internal redundant copy used to improve robustness and detect potential mismatches.

### Voltage Monitoring

The integrated ADC allows battery terminal voltage monitoring with a high degree of accuracy. The FFG3105 has been designed for integration into the battery pack, which allows it to directly measure the cell voltage. This allows the host system to know what the voltage is at the battery cell. It eliminates the uncertainty introduced by system side gauge measurements, which include series resistance of the protection circuitry, pack terminals and series trace resistance. To achieve optimal charging performance it is important for the host to accurately know the internal cell voltage.

### Temperature Sensing and Reporting

The FFG3105 measures the battery temperature using its on board temperature sensor. This temperature information can be used to improve battery-charging performance. Accurate understanding of the battery temperature is critical to maintain optimal charging rates and to ensure safe operation during high current charging. The FFG3105 temperature sensor is accurate to within  $\pm 3^{\circ}\text{C}$  over the operating ranges that support battery charging.

### User Definable Registers

The FFG3105 includes twelve 16-bit registers, which can be written to and read by the host. These registers are provided to allow important history or other user information to be stored in the battery pack. If used in conjunction with the FFG1040, Fuel Gauge, the FFG3105 registers can be used to support the FFG1040's save and restore feature, by storing critical battery parameters and fuel gauging information. This information is used when a battery is removed and re-inserted or when a user swaps between several batteries.

With the ability to identify the battery and store fuel gauging history, the system side fuel gauge can initialize with zero learning time to achieve optimal accuracy. The FFG3105 is powered directly from the battery pack's internal terminal voltage. Therefore, the values in the FFG3105 registers are retained even when the battery voltage drops below the systems shut down voltage. If the battery voltage drops below the battery protection threshold and the battery is locked out, the FFG3105 loses power and the values in these registers are lost.

### Programming the 64-Bit ID Code

The FFG3105 includes two 64-bit, one-time, eFuse programmable registers to allow for a unique ID code to be permanently stored in this register.

Programming the FFG3105 requires knowledge of the Lock and Unlock keywords. The appropriate lock and unlock 32-bit keyword must be written to the KEYWORD\_MSW, KEYWORD\_LSW registers before a Lock or Unlock command is issued and programming is attempted.

When programmed, a redundant copy is created. The redundant copy is used when the BID is read back to improve robustness and detect errors.

These register can be programmed and verified by Fairchild before shipping or with the proper procedure be programmed by the customer before the battery cell is attached. Please contact your Fairchild sales representative to set the custom code for your application or to receive detailed information on programming the FFG3105.

### Power Modes

The FFG3105 chip has three power modes, ACTIVE, STANDBY and SHUTDOWN. The FFG3105 moves in and out of these modes automatically based on requests from the Host for voltage and temperature readings and the external chip enable, **CE**.

#### Standby Power Mode

During periods of inactivity when the host is not requesting voltage or temperature readings the FFG3105 enters STANDBY mode to save power. In STANDBY, the FFG3105, the I<sup>2</sup>C bus, and registers are still available and accessible. The Host may read or write the User Definable registers while in STANDBY.

#### Active Power Mode

The FFG3105 enters this mode when the host requests a measurement of the battery voltage or temperature. It takes < 28 ms for the FFG3105 to measure both voltage and temperature and write them into the output registers. The measure automatically moves the device to ACTIVE. After the measurements are made the device returns to STANDBY on its own.

#### Shutdown Mode and Chip Enable

The FFG3105 has an active high chip enable, **CE**, which must be high for chip to function in either STANDBY or ACTIVE modes. When the FFG3105 is used internal to the battery pack, this pin is connected to the gate driver of the protection device used to control the discharge FET. This signal is high whenever the battery pack is functioning within acceptable operating range.

When the FET is turned-off to protect the battery cell the FFG3105 is also disabled and goes to its lowest power condition, SHUTDOWN. This helps to reduce the under-voltage discharge the FFG3105 applies to the internal cell. All internal current paths from **VCELP**, the chip supply, to **GND**, which drain the battery cell, are turned

off when **CE** = 0 to guarantee a typical quiescent current of ≤ 1 μA.

#### Wake and Sleep

The FFG3105 also supports WAKE and SLEEP modes that can be used for system debug. In WAKE mode the entire device is turned on and left on until the SLEEP mode is requested. In WAKE mode the internal Bandgap, Oscillator and LDO are enabled and the current increases.

#### Calculating Average Power

Average power consumption of the FFG3105 is a function of the frequency of voltage and temperature read requests. During measurement time the FFG3105 uses 180 μA, when at rest, in STANDBY it uses 2 μA.

Average power consumption can be calculated using the following equation and graphic.

$$\text{Average Current} \approx (180\mu\text{A} \times 0.0256\text{s} + 58\mu\text{A} \times 0.0005\text{s} + 2.0\mu\text{A} \times (Tr - 0.0256\text{s} - 0.0005\text{s}))/Tr \quad (1)$$

where *Tr* = Time between read requests in seconds (S)

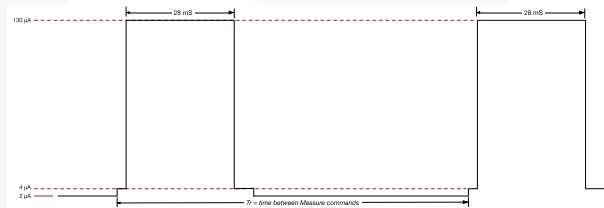


Figure 5. Timing Relationship Diagram

For example, if the system were to request voltage and temperature readings from the FFG3105 once every 6 seconds, the average power would be:

$$\text{Average Current} \approx (180\mu\text{A} \times 0.0256\text{s} + 58\mu\text{A} \times 0.0005\text{s} + 2.0\mu\text{A} \times (6\text{s} - 0.0256\text{s} - 0.0005\text{s}))/6\text{s} \quad (2)$$

$$\text{Average Current} = 4.9 \mu\text{A} \quad (3)$$

For a case where the Host system requests voltage and temperature once per second, the average current is 6.06 μA. A summary of the active current vs. sampling interval is shown in Figure 6.

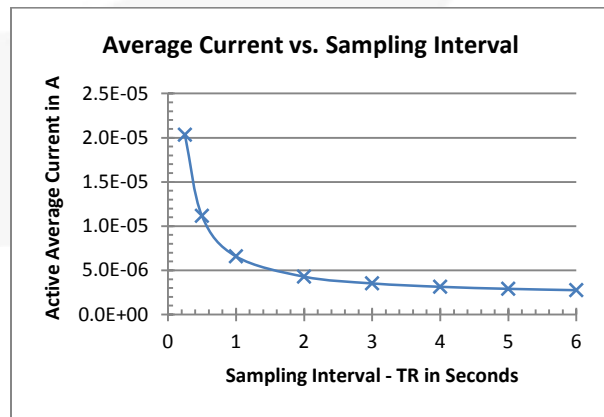


Figure 6. Average Active Current

## Battery and Device Protection

### Cell Protection

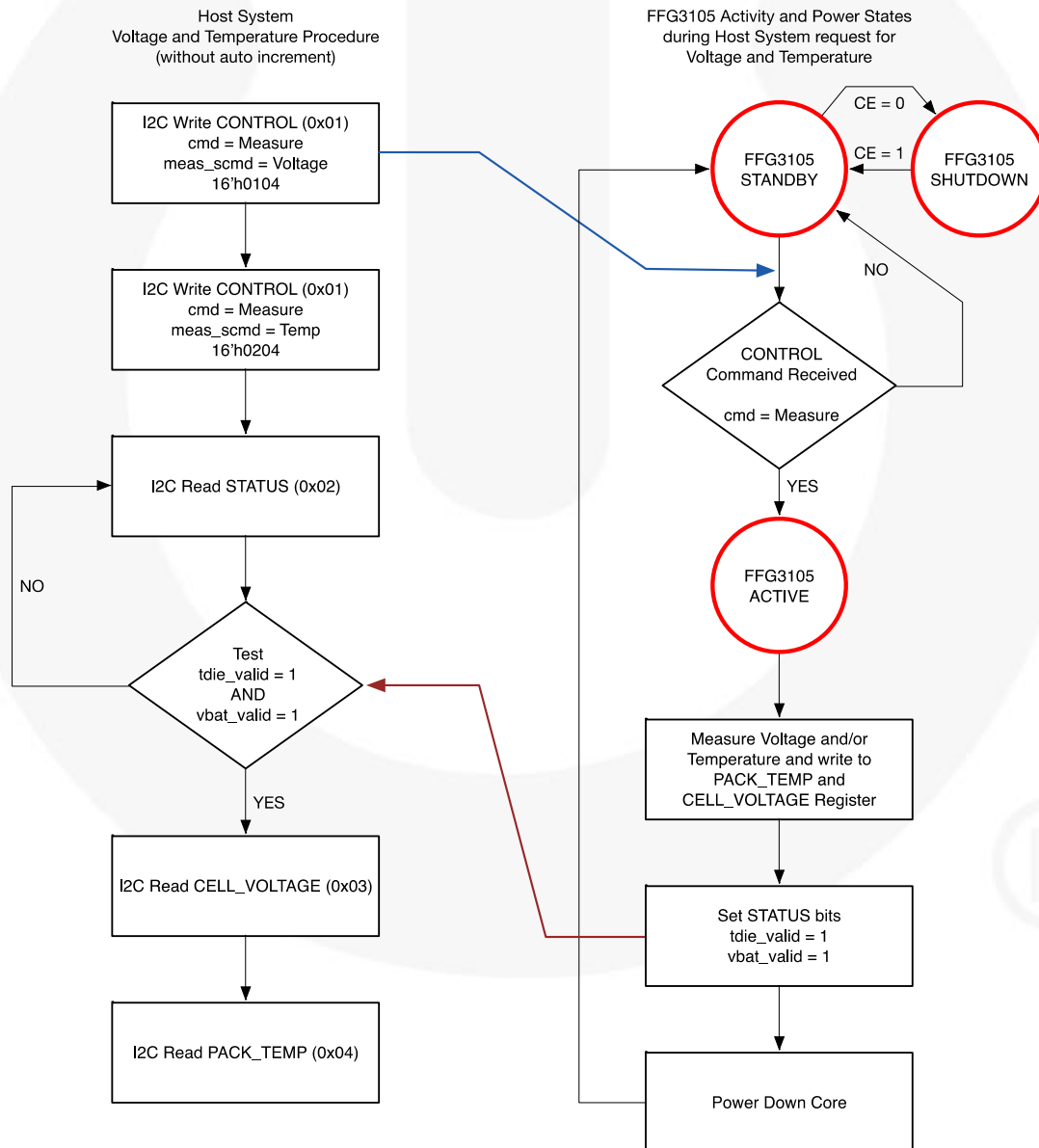
The FFG3105 has been designed to be integrated directly into a single-cell Lithium-ion battery pack and meet all the necessary safety requirements. This is accomplished by having separate terminals (**VCELP** and **VSNS**) to power the device, and sense the cell voltage respectively. Each of these connections to the battery cell requires a series resistor to limit the current if an internal short occurs. This is needed because the FFG3105 is connected directly to the cell cathode and anode. Additional filter capacitors may also be required. It is recommended that series capacitors be used to eliminate a single capacitor short from shorting out the cell.

### Input ESD Protection

In a removable battery pack, **SCL** and **SDA**, the I2C clock and data pins of the host bus are externally exposed. It is recommended that a protection network consisting of a Zener diode and resistors, or some equivalent, be connected to the serial interface pins to protect the pack from ESD events.

The maximum pull-up voltage of 5.5 V is supported for device programming, so it is recommended that the breakdown voltage of the protection device be > 5.6 V.

The devices needed for cell and ESD protection are represented in the schematic in Figure 1.



**Figure 7. Voltage and Temperature Data Request**

## Device Programming

The FFG3105 has two 64-bit battery identifications values that can be programmed into the device. This section outlines the procedure that should be followed to program the device.

### Keyword Registers

The device must first be unlocked by writing the 32-bit Keyword with the appropriate value into KEYWORD\_MSW and KEYWORD\_LSW registers at I<sup>2</sup>C addresses 0x06 and 0x07. Next an Unlock command must be written to the CONTROL register to perform the Unlock. This enables the user to write into the BID registers.

### BID Registers

Each BID uses four 16-bit registers that total 64-bits. The first BID, BID0, is located at I<sup>2</sup>C address 0x20, 0x21, 0x22, and 0x23. The second BID, BID1 is located at 0x24, 0x25, 0x26, and 0x27. Once unlocked one or both of these BID must be written and then verified by reading it back.

### Programming

Once the BID's have been verified the Program command is issued using an I<sup>2</sup>C write to the CONTROL register. Before issuing the Program command the supply voltage,  $V_{CEL P}^{(18)}$ , must be increased to 5.5 V. Once programming has been initiated an internal state machine controls the part and completes the programming process. Programming both BID's takes approximately 5.2 ms but the actual time will depend on the number of 1's in the BID codes.

Reading the TEST\_STATUS register bit fuse\_prgm\_done can monitor the status of the programming sequence. Once completed this bit is set to 1.

### Verification

Once programmed, the voltage is lowered back to 3.8 V and reset. After reset the BID's can be read and their internal status checks to determine if the programming was successful.

### Note:

18.  $V_{CEL P}$  should be capable of supplying a minimum of 61 mA.

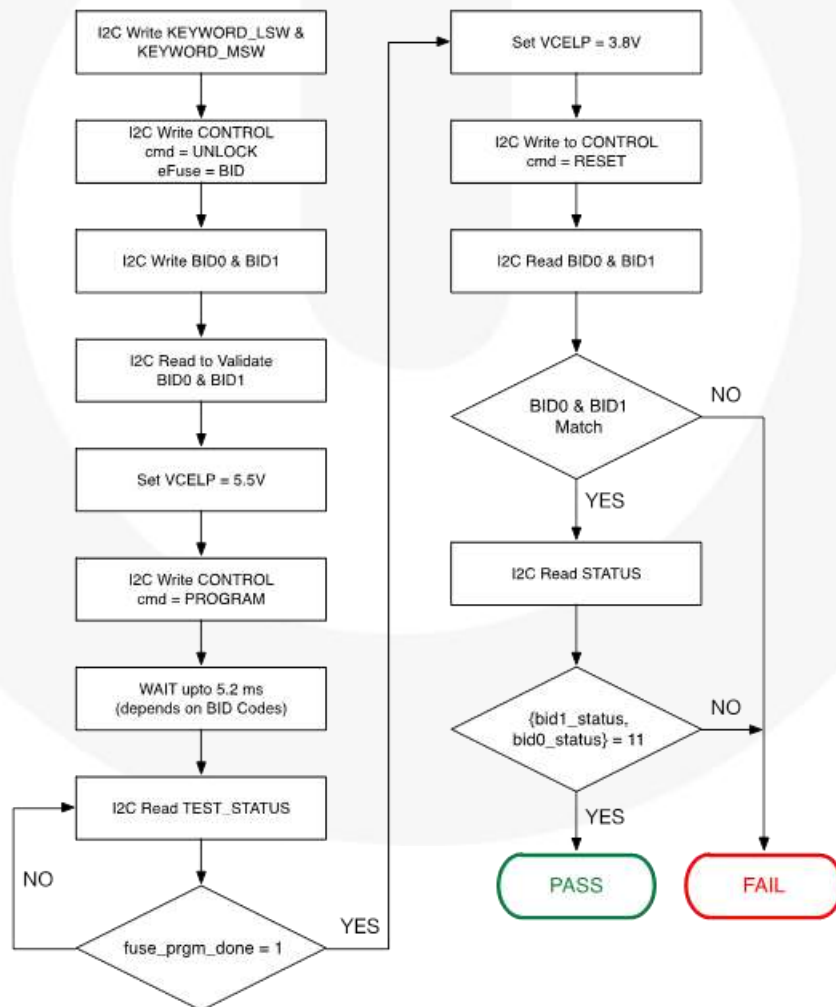


Figure 8. Device Programming

## I<sup>2</sup>C Interface

The I<sup>2</sup>C interface is slave controllers with a standard 7-bit device address that supports read, incremental read, write and incremental write. This allows an external host to control the FFG3105 and configure it.

The I<sup>2</sup>C supports:

- 7-Bit Standard Device Address
- 100 kbit/s Standard Mode
- 400 kbit/s Fast Mode
- Auto Increment to support Burst-Reads and Burst-Writes for the most used registers.

The FFG3105's **SCL** line is an input and its **SDA** line is a bi-directional open-drain output; it can only pull down the bus when active. The **SDA** line only pulls LOW during data reads and when signaling ACK. All data is shifted in MSB (bit 7) first.

### Slave Address

The I<sup>2</sup>C Device ID is 7-bits and is constructed as shown in the table below. There is always an 8<sup>th</sup> bit, which indicates if the operation being done to the slave is either a read or write. A read is active-high and indicated by '1', the write is active-low and indicated by a '0'.

The slave device ID will be configurable with a device ID at address 8'h6E for write and 8'h6F for read.

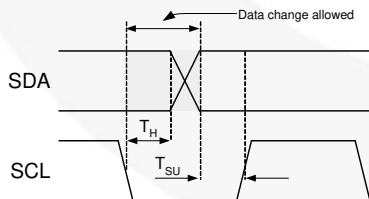
**Table 2. I<sup>2</sup>C Slave Address Byte**

Bit	7	6	5	4	3	2	1	0
Value	0	1	1	0	1	1	1	R/W

Other slave addresses can be accommodated upon request. Contact your Fairchild representative.

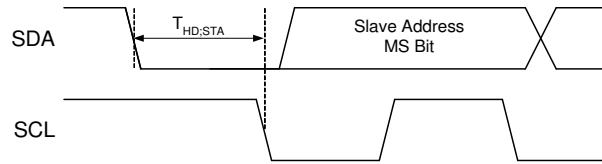
### Bus Timing

As shown in Figure 9, data is normally transferred when **SCL** is LOW. Data is clocked in on the rising edge of **SCL**. Typically, data transitions at or shortly after the falling edge of **SCL** to allow ample time for the data to set up before the next **SCL** rising edge.



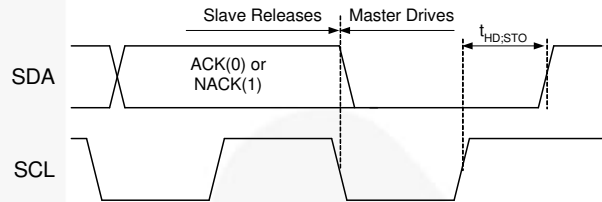
**Figure 9. Data Transfer Timing**

Each bus transaction begins and ends with **SDA** and **SCL** HIGH. A transaction begins with a START condition, which is defined as **SDA** transitioning from 1 to 0 with **SCL** HIGH.



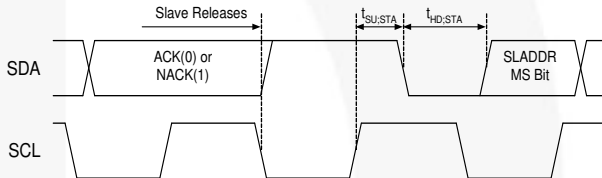
**Figure 10. START Bit**

A transaction ends with a STOP condition, which is defined as **SDA** transitioning from 0 to 1 with **SCL** HIGH.



**Figure 11. STOP Bit**

During a read from the FFG3105, the master issues a Repeated Start after sending the register address and before resending the slave address. The Repeated Start is a 1-to-0 transition on **SDA** while **SCL** is HIGH.



**Figure 12. Repeated STOP Timing**

### Auto-Incrementing

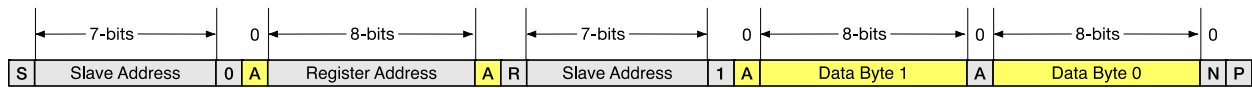
The external host can also utilize auto-increment to do sequential reads or writes of the internal registers.

When the auto-incremented address is not with the supported range of registers one of four responses can be expected.

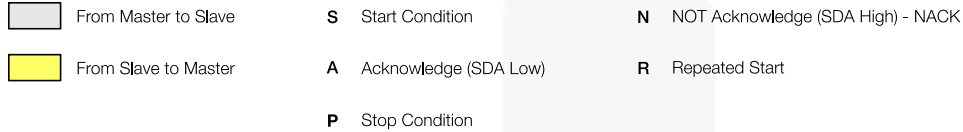
- If write or read is to an illegal or out of range address the response to the host is a NACK.
- If a write auto increments to an out of range address the response to the host is a NACK.
- If a read auto increment to an out of range address the read returns data with a value of 0xFFFF.

## I<sup>2</sup>C Read Write Procedures

The following figures illustrate compatible I<sup>2</sup>C write and read sequences.

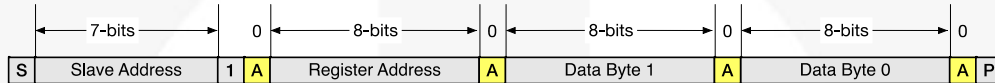


**Note:** Register address to read is specified with write. If register is not specified Master will begin read from the current register.

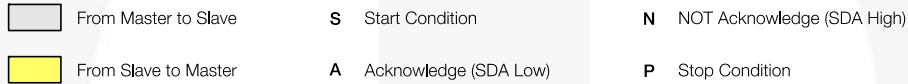


**Figure 13. I<sup>2</sup>C Read Sequence**

During an I<sup>2</sup>C read, the master must acknowledge the first byte read for proper operation. Missing or corrupted clocks during an I<sup>2</sup>C operation, may result in the FFG3105 continuously asserting the SDA line. The I<sup>2</sup>C master must support the Bus Clear operation in systems where SCL integrity is not guaranteed (for example in systems with a removable battery pack which can result in interrupted I<sup>2</sup>C transactions).



**Note:** Single register read is initiated by Master with P immediately following second data byte



**Figure 14. I<sup>2</sup>C Write Sequence**

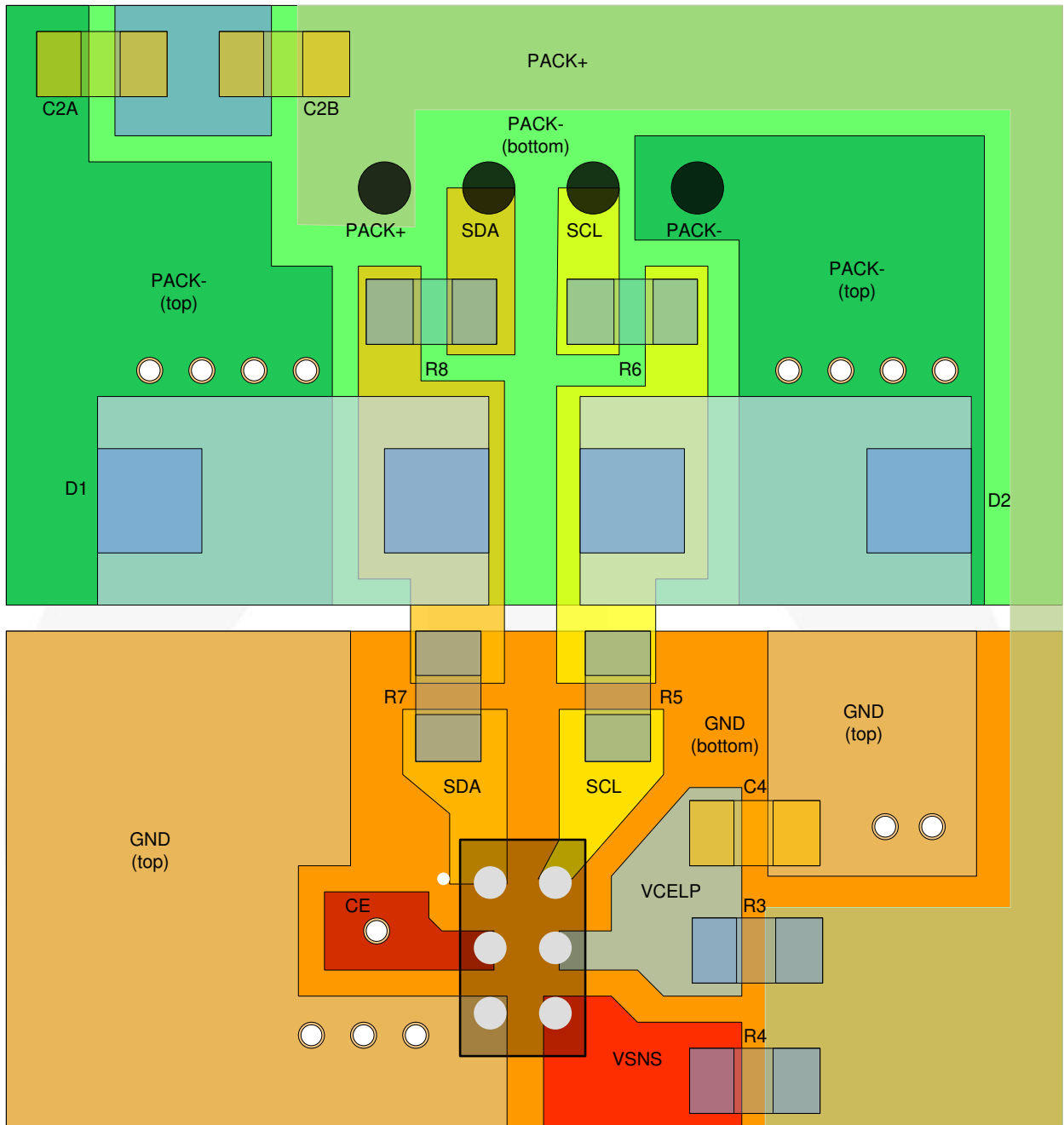


Figure 15. Recommended Layout

## Register Information

Any registers or bit fields marked as RESERVED or reserved should be left at their default values and not modified.

**Table 3. Register Map**

Registers			
Register Name	Address	Type	Description
PART_ID	0x00	RO	Part Identification
CONTROL	0x01	R/W	Control
STATUS	0x02	RO	Status
CELL_VOLTAGE	0x03	RO	Cell Voltage Measurement
PACK_TEMPERATURE	0x04	RO	Pack Temperature
CELL_CURRENT	0x05	N/A	Reserved for future use
KEYWORD_LSW	0x06	R/W	Keyword Least Significant Word
KEYWORD_MSW	0x07	R/W	Keyword Most Significant Word
TEST_CONTROL	0x08	R/W	Test Control
TEST_STATUS	0x09	RO	Test Status
SPARE	0x0A	R/W	Spare
USER_00 – USER_11	0x10-0x1B	R/W	User Configurable
BATTERY_ID0	0x20-0x23	R/W	Unique Identification Code 0
BATTERY_ID1	0x24-0x27	R/W	Unique Identification Code 1
RESERVED	0x30-0x57	-	Reserved

## Control and Status Registers for Mission Mode and Test

The registers in this section are used to store information used, created, and maintained by the top level of the chip. They are defined in the address range 0x00 – 0x0A. These registers are powered by the battery and can be written or read when the core is asleep or awake.

**Table 4. PART\_ID Register (0x00)**

Bit Name	Bit	Type	Default	Description
rev_id[2:0]	2:0	RO	3'b000	Device Revision
part_id[4:0]	7:3	RO	5'b10000	Part Identification
device_id[7:0]	15:8	RO	8'h6E	I <sup>2</sup> C Device ID



**Table 5. CONTROL Register (0x01)**

Bit Name	Bit	Type	Default	Description
command	3:0	R/W/SC	4'b0000	Device Command 0000 – NOP (used with TEST_CONTROL) 0001 – Wake 0010 – Sleep 0011 – Program (eFuse) 0100 – Measure 0101 – Lock eFuse Group 0110 – Unlock eFuse Group 0111 – Reset 1000 – Reserved 1001 – Reserved 1010 – Reserved 1011 – Reserved 1100 – Reserved 1101 – Reserved 1110 – Reserved 1111 – Test (reserved)
eFuse_group	5:4	R/W	2'b00	Block Group for Lock/Unlock 00 – None 01 – BID 10 – AFE Trim 11 – Reserved Note: Only applies with commands 0x5 and 0x6
reserved	7:6	R/W	2'b00	Reserved
The following fields are based on the command chosen				
Commands: <b>NOP, Wake, Sleep, Lock, Unlock, Reset, Program</b>				
reserved	15:8	R/W	8'h00	N/A
Commands: <b>Measure</b>				
meas_scmd[2:0]	8	R/W	1'b0	Measure Source Sub Command Bit-0 0 – No voltage measurement 1 – Measure Voltage
	9	R/W	1'b0	Measure Source Sub Command Bit-1 0 – No temperature measurement 1 – Measure Temperature
	10	R/W	1'b0	Measure Source Sub Command Bit-2 0 – No current measurement 1 – Measure Current (Not implemented in FFG3105)
meas_scmd[7:3]	15:11	R/W	5'b00000	Can be treated as “Don’t Cares”
Commands: <b>Test</b>				
test_scmd[2:0]	11:8	R/W	4'b0000	Reserved
reserved	15:12	R/W	4'b0000	Can be treated as “Don’t Cares”

**Table 6. STATUS Register (0x02)**

Type	Bit	Type	Default	Description
wake_status	0	RO	1'b0	Core Power Status 0 – AFE core is asleep. 1 – AFE core is awake.
busy_status	1	RO	1'b0	Busy Status 0 – chip core is not busy 1 – chip core is busy
keep_aware	2	RO	1'b0	Keep Awake 0 – core is not kept awake 1 – core is to be kept awake
tdie_valid	3	RO	1'b0	Die Temperature Measurement Valid 0 – current pack temperature invalid 1 – current pack temperature valid
vbat_valid	4	RO	1'b0	Battery Voltage Measurement Valid 0 – current cell voltage invalid 1 – current cell voltage valid
ibat_valid (reserved)	5	RO	1'b0	Battery Current Measurement Valid 0 – current cell current invalid 1 – current cell current valid
bid_lock_status	6	RO	1'b1	Battery ID Lock Status 0 – unlocked 1 – locked
at_lock_status	7	RO	1'b1	AFE Trim Lock Status 0 – unlocked 1 – locked
bid0_status	8	RO	1'b0	BID0 Status 0 – BID0 Redundancy Check Failed 1 – BID0 Redundancy Check Passed
bid1_status	9	RO	1'b0	BID1 Status 0 – BID1 Redundancy Check Failed 1 – BID1 Redundancy Check Passed
reserved	15:8	RO	8'hXX	Reserved

**Table 7. CELL\_VOLTAGE Register (0x03)**

Type	Bit	Type	Default	Description
cell_voltage	15:0	RO	16'h0000	Battery Voltage Measurement Unsigned Short MSB = $a[15] = 2^2 = 4 \text{ V}$ LSB = $a[0] = 2^{-13} = 122.07 \mu\text{V}$ +FS = $16'b1111111111111111 = 7.99987793 \text{ V}$ -FS = $16'b0000000000000000 = 0 \text{ V}$

**Table 8. PACK\_TEMPERATURE Register (0x04)**

Type	Bit	Type	Default	Description
pack_temperature	15:0	R	16'h0000	Temperature Measurement Signed Short MSB = $a[15] = -2^8 = -256 \text{ mV}$ LSB = $a[4] = 2^{-3} = 0.125 \text{ mV}$ +FS = $255.9921875 \text{ mV}$ -FS = $-255.9921875 \text{ mV}$

**Table 9. CELL\_CURRENT Register (0x05)**

Type	Bit	Type	Default	Description
cell_current	15:0	R	16'h0000	Reserved

**Note:**

19. Not supported in the FFG3105.

**Table 10. KEYWORD\_LSW Register (0x06)**

Type	Bit	Type	Default	Description
keyword[15:0]	15:0	R/W	16'hFFFF	Protection Keyword Least Significant Word

**Table 11. KEYWORD\_MSW Register (0x07)**

Type	Bit	Type	Default	Description
keyword[31:0]	15:0	R/W	16'h0000	Protection Keyword Most Significant Word

**Table 12. TEST\_CONTROL Register (0x08)**

Type	Bit	Type	Default	Description
reserved	15:0	R/W	16'h0000	Reserved

**Table 13. TEST\_STATUS Register (0x09)**

Type	Bit	Type	Default	Description
reserved	15:0	RO	16'h0000	Reserved

**Table 14. SPARE Register (0x0A)**

Type	Bit	Type	Default	Description
User Defined	15:0	R/W	16'h0000	Spare scratch pad register

## User Battery Parameter Registers

The 12 registers in this section can be used to hold the Save/Restore content of the FFG1040. If the FFG3105 is not used with the FFG1040, these become user definable registers. These registers sit in the **VCELP** domain and retain their value if the battery pack has been properly charged and does not experience an over-discharge or over-current condition.

These registers can be written or read when the core is asleep or awake.

**Table 15. USER\_00 – USER\_011 - Register (0x10 – 0x1B)**

Type	Bit	Type	Default	Description
User Defined	15:0	R/W	16'h0000	12 User Defined R/W registers

## Battery Identification Registers

These two sets of four 16-bit registers are assigned to hold two 64-bit battery identifications. These should be concatenated such that  $BID0[63:0] = \{BID\_03[15:0], BID\_02[15:0], BID\_01[15:0], BID\_00[15:0]\}$  and  $BID1[63:0] = \{BID\_13[15:0], BID\_12[15:0], BID\_11[15:0], BID\_10[15:0]\}$ . These registers can only be written when the core is awake and  $wake\_status = 1'b1$ . They can be read when the core is asleep or awake.

**Table 16. BID\_00 Register (0x020)**

Type	Bit	Type	Default	Description
bid_data_00[15:0]	15:0	RO	16'h0000	Battery ID 0 Register – Bytes 0 & 1

**Table 17. BID\_01 Register (0x021)**

Type	Bit	Type	Default	Description
bid_data_01[31:16]	15:0	RO	16'h0000	Battery ID 0 Register – Bytes 2 & 3

**Table 18. BID\_02 Register (0x022)**

Type	Bit	Type	Default	Description
bid_data_02[47:32]	15:0	RO	16'h0000	Battery ID 0 Register – Bytes 4 & 5

**Table 19. BID\_03 Register (0x023)**

Type	Bit	Type	Default	Description
bid_data_03[63:48]	15:0	RO	16'h0000	Battery ID 0 Register – Bytes 6 & 7

**Table 20. BID\_10 Register (0x024)**

Type	Bit	Type	Default	Description
bid_data-10[15:0]	15:0	RO	16'h0000	Battery ID 1 Register – Bytes 0 & 1

**Table 21. BID\_11 Register (0x025)**

Type	Bit	Type	Default	Description
bid_data_11[31:16]	15:0	RO	16'h0000	Battery ID 1 Register – Bytes 2 & 3

**Table 22. BID\_12 Register (0x026)**

Type	Bit	Type	Default	Description
bid_data_12[47:32]	15:0	RO	16'h0000	Battery ID 1 Register – Bytes 4 & 5

**Table 23. BID\_13 Register (0x027)**

Type	Bit	Type	Default	Description
bid_data_13[63:48]	15:0	RO	16'h0000	Battery ID 1 Register – Bytes 6 & 7

### Notes:

20. R/W = register value may be read or written.

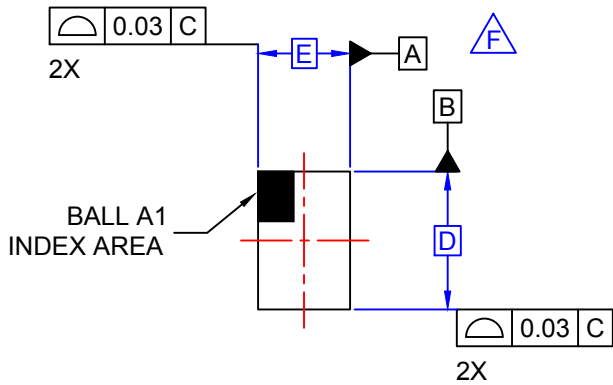
21. RO = register value that should only be read; attempting a write may cause unpredictable behavior.

22. R/W1CO = register value may be read; writing a 1 clears a bit in another register.

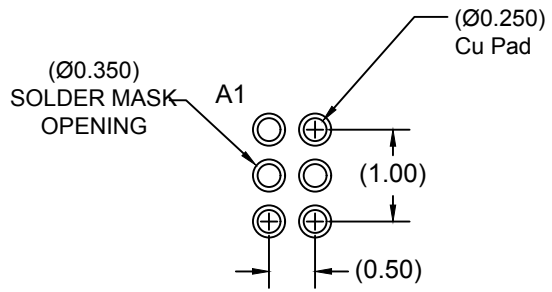
The table below pertains to the Marketing Outline drawing on the following page.

### Product Specific Dimensions

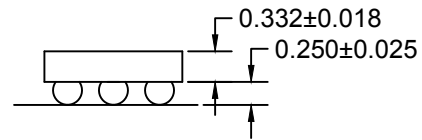
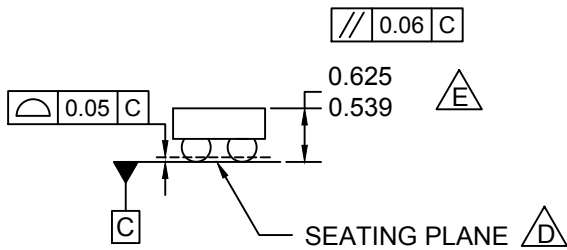
E (mm)	D (mm)	X (mm)	Y (mm)
0.960 ± 0.030	1.660 ± 0.030	0.230 ± 0.018	0.330 ± 0.018



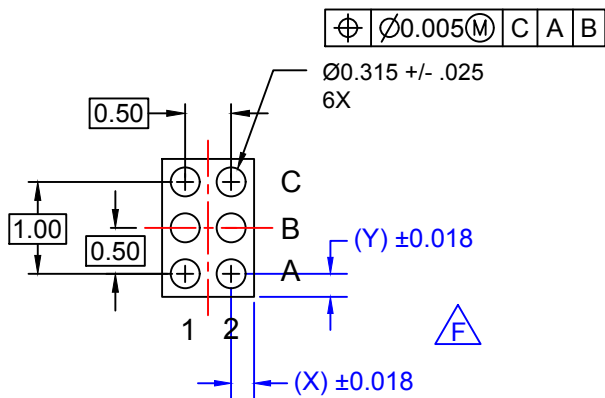
TOP VIEW



RECOMMENDED LAND PATTERN  
(NSMD PAD TYPE)



SIDE VIEWS




BOTTOM VIEW

NOTES:

- A. NO JEDEC REGISTRATION APPLIES.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCE PER ASMEY14.5M, 1994.
- D. DATUM C IS DEFINED BY THE SPHERICAL CROWNS OF THE BALLS.
- E. PACKAGE NOMINAL HEIGHT IS 582 MICRONS ±43 MICRONS (539-625 MICRONS).
- F. FOR DIMENSIONS D, E, X, AND Y SEE PRODUCT DATASHEET.
- G. DRAWING FILNAME: MKT-UC006AFrev3.



ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910  
**Japan Customer Focus Center**  
Phone: 81-3-5817-1050

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)  
**Order Literature:** <http://www.onsemi.com/orderlit>  
For additional information, please contact your local  
Sales Representative